

OKI Semiconductor**MSM51V18160A**

1,048,576-Word x 16-Bit DYNAMIC RAM : FAST PAGE MODE TYPE

DESCRIPTION

The MSM51V18160A is a 1,048,576-word x 16-bit Dynamic RAM fabricated in OKI's CMOS silicon gate technology.

The MSM51V18160A achieve high integration, high-speed operation, and low-power consumption, due to quadruple polysilicon double metal CMOS.

The MSM51V18160A is available in a 42-pin SOJ or 50/44-pin plastic TSOP.

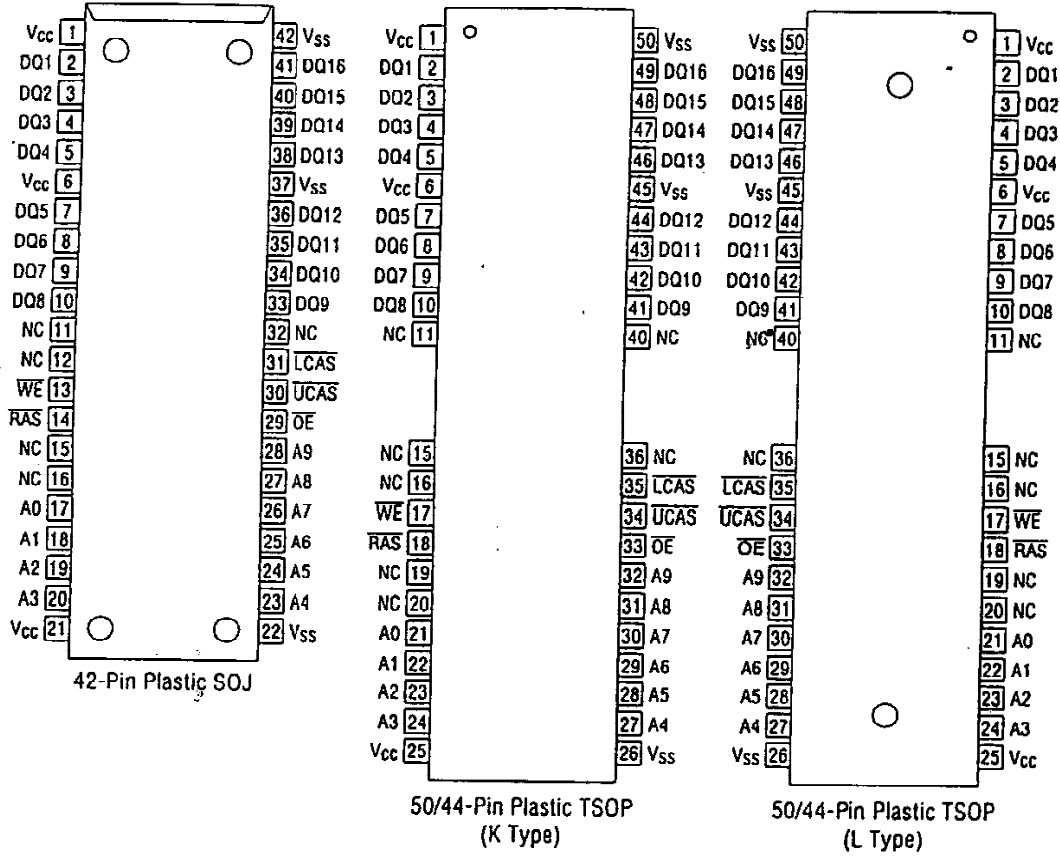
FEATURES

- 1,048,576-word x 16-bit configuration
 - Single 3.3 V power supply, ± 0.3 V tolerance
 - Input : LVTTTL compatible, low input capacitance
 - Output : LVTTTL compatible, tristate
 - Refresh : 1024 cycles/16 ms
 - $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh, Hidden refresh, $\overline{\text{RAS}}$ -only refresh capability
 - Package:
 - 42-Pin 400 mil Plastic SOJ (SOJ42-P-400) (Product : MSM51V18160A-xxJS)
 - 50/44-Pin 400 mil Plastic TSOP (TSOP50/44-P-400/0.8-K) (Product : MSM51V18160A-xxTS-K)
 - (TSOP50/44-P-400/0.8-L) (Product : MSM51V18160A-xxTS-L)
- xx indicates speed rank.

PRODUCT FAMILY

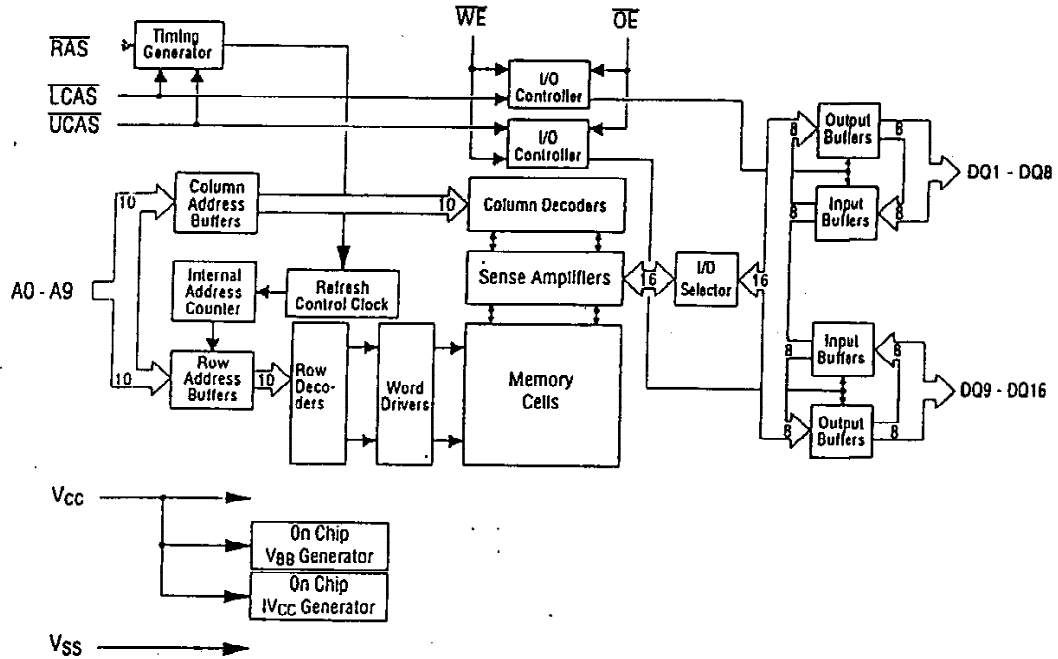
Family	Access Time (Max.)				Cycle Time (Min.)	Power Dissipation	
	t _{RAC}	t _{AA}	t _{CAC}	t _{OEA}		Operating (Max.)	Standby (Max.)
MSM51V18160A - 60	60 ns	30 ns	15 ns	15 ns	110 ns	684mW	3.6 mW
MSM51V18160A - 70	70 ns	35 ns	20 ns	20 ns	130 ns	648mW	
MSM51V18160A - 80	80 ns	40 ns	20 ns	20 ns	150 ns	612mW	

PIN CONFIGURATION (TOP VIEW)



Pin Name	Function
A0 - A9	Address Input
RAS	Row Address Strobe
LCAS	Lower Byte Column Address Strobe
UCAS	Upper Byte Column Address Strobe
DQ1 - DQ16	Data Input/Data Output
OE	Output Enable
WE	Write Enable
Vcc	Power Supply (3.3 V)
Vss	Ground (0 V)
NC	No Connection

BLOCK DIAGRAM



FUNCTION TABLE

Input Pin					DQ Pin		Function Mode
RAS	LCAS	UCAS	WE	OE	DQ1 - DQ8	DQ9 - DQ16	
H	•	•	•	•	High-Z	High-Z	Standby
L	H	H	•	•	High-Z	High-Z	Refresh
L	L	H	H	L	Dout	High-Z	Lower Byte Read
L	H	L	H	L	High-Z	Dout	Upper Byte Read
L	L	L	H	L	Dout	Dout	Word Read
L	L	H	L	H	Din	Don't Care	Lower Byte Write
L	H	L	L	H	Don't Care	Din	Upper Byte Write
L	L	L	L	H	Din	Din	Word Write
L	L	L	H	H	High-Z	High-Z	—

ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Voltage on Any Pin Relative to V_{SS}	V_T	-0.5 to 4.6	V
Short Circuit Output Current	I_{OS}	50	mA
Power Dissipation	P_D^*	1	W
Operating Temperature	T_{opr}	0 to 70	°C
Storage Temperature	T_{stg}	-55 to 150	°C

*: $T_a = 25^\circ\text{C}$

Recommended Operating Conditions

 $(T_a = 0^\circ\text{C to } 70^\circ\text{C})$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Power Supply Voltage	V_{CC}	3.0	3.3	3.6	V
	V_{SS}	0	0	0	V
Input High Voltage	V_{IH}	2.0	—	$V_{CC} + 0.3$	V
Input Low Voltage	V_{IL}	-0.3	—	0.8	V

Capacitance

 $(V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}, T_a = 25^\circ\text{C}, f = 1 \text{ MHz})$

Parameter	Symbol	Typ.	Max.	Unit
Input Capacitance (A0 - A9)	C_{IN1}	—	5	pF
Input Capacitance (RAS, LCAS, UCAS, WE, OE)	C_{IN2}	—	7	pF
Output Capacitance (DQ1 - DQ16)	C_{VO}	—	7	pF

DC Characteristics

 $(V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}, T_a = 0^\circ\text{C to } 70^\circ\text{C})$

Parameter	Symbol	Condition	MSM51V18160 A -60		MSM51V18160 A -70		MSM51V18160 A -80		Unit	Note
			Min.	Max.	Min.	Max.	Min.	Max.		
			Output High Voltage	V_{OH}	$I_{OH} = -1.0 \text{ mA}$	2.4	V_{CC}	2.4		
Output Low Voltage	V_{OL}	$I_{OL} = 1.0 \text{ mA}$	0	0.4	0	0.4	0	0.4	V	
Input Leakage Current	I_{LI}	$0 \text{ V} \leq V_I \leq V_{CC} + 0.3 \text{ V}$; All other pins not under test = 0 V	-10	10	-10	10	-10	10	μA	
Output Leakage Current	I_{LO}	DQ disable $0 \text{ V} \leq V_O \leq 3.6 \text{ V}$	-10	10	-10	10	-10	10	μA	
Average Power Supply Current (Operating)	I_{CC1}	$\overline{\text{RAS}}, \overline{\text{CAS}}$ cycling, $t_{RC} = \text{Min.}$	—	190	—	180	—	170	mA	1, 2
Power Supply Current (Standby)	I_{CC2}	$\overline{\text{RAS}}, \overline{\text{CAS}} = V_{IH}$	—	2	—	2	—	2	mA	1
		$\overline{\text{RAS}}, \overline{\text{CAS}}$ $\geq V_{CC} - 0.2 \text{ V}$	—	1	—	1	—	1	mA	1
Average Power Supply Current (RAS-only Refresh)	I_{CC3}	$\overline{\text{RAS}}$ cycling, $\overline{\text{CAS}} = V_{IH}$, $t_{RC} = \text{Min.}$	—	190	—	180	—	170	mA	1, 2
Power Supply Current (Standby)	I_{CC5}	$\overline{\text{RAS}} = V_{IH}$, $\overline{\text{CAS}} = V_{IL}$, DQ = enable	—	5	—	5	—	5	mA	1
Average Power Supply Current ($\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ Refresh)	I_{CC6}	$\overline{\text{RAS}}$ cycling, $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$	—	190	—	180	—	170	mA	1, 2
Average Power Supply Current (Fast Page Mode)	I_{CC7}	$\overline{\text{RAS}} = V_{IL}$, $\overline{\text{CAS}}$ cycling, $t_{PC} = \text{Min.}$	—	170	—	160	—	150	mA	1, 3

- Notes :
1. I_{CC} Max. is specified as I_{CC} for output open condition.
 2. Address can be changed once or less while $\overline{\text{RAS}} = V_{IL}$.
 3. Address can be changed once or less while $\overline{\text{CAS}} = V_{IH}$.

AC Characteristics (1/2)

(V_{CC} = 0.3 V ± 3.3 V, T_a = 0°C to 70°C) Note 1, 2, 3

Parameter	Symbol	MSM51V18160		MSM51V18160		MSM51V18160		Unit	Note
		A -60		A -70		A -80			
		Min.	Max.	Min.	Max.	Min.	Max.		
Random Read or Write Cycle Time	t _{RC}	110	—	130	—	150	—	ns	
Read Modify Write Cycle Time	t _{RWC}	150	—	180	—	200	—	ns	
Fast Page Mode Cycle Time	t _{PC}	40	—	45	—	50	—	ns	
Fast Page Mode Read Modify Write Cycle Time	t _{PRWC}	80	—	95	—	100	—	ns	
Access Time from RAS	t _{RAC}	—	60	—	70	—	80	ns	4, 5, 6
Access Time from CAS	t _{CAC}	—	15	—	20	—	20	ns	4, 5
Access Time from Column Address	t _{AA}	—	30	—	35	—	40	ns	4, 6
Access Time from CAS Precharge	t _{CPA}	—	35	—	40	—	45	ns	4, 12
Access Time from OE	t _{OEa}	—	15	—	20	—	20	ns	4
Output Low Impedance Time from CAS	t _{CLZ}	0	—	0	—	0	—	ns	4
CAS to Data Output Buffer Turn-off Delay Time	t _{OFF}	0	15	0	15	0	15	ns	7
OE to Data Output Buffer Turn-off Delay Time	t _{OEZ}	0	15	0	15	0	15	ns	7
Transition Time	t _T	3	50	3	50	3	50	ns	3
Refresh Period	t _{REF}	—	16	—	16	—	16	ms	
RAS Precharge Time	t _{RP}	40	—	50	—	60	—	ns	
RAS Pulse Width	t _{RAS}	60	10,000	70	10,000	80	10,000	ns	
RAS Pulse Width (Fast Page Mode)	t _{RASP}	60	100,000	70	100,000	80	100,000	ns	
RAS Hold Time	t _{RSH}	15	—	20	—	20	—	ns	
RAS Hold Time referenced to OE	t _{ROH}	15	—	20	—	20	—	ns	
CAS Precharge Time (Fast Page Mode)	t _{CP}	10	—	10	—	10	—	ns	14
CAS Pulse Width	t _{CAS}	15	10,000	20	10,000	20	10,000	ns	
CAS Hold Time	t _{CSH}	60	—	70	—	80	—	ns	
CAS to RAS Precharge Time	t _{CRP}	5	—	5	—	5	—	ns	12
CAS to RAS Precharge Time	t _{RHCP}	35	—	40	—	45	—	ns	12
RAS to CAS Delay Time	t _{RCd}	20	45	20	50	20	60	ns	5
RAS to Column Address Delay Time	t _{RAD}	15	30	15	35	15	40	ns	6
Row Address Set-up Time	t _{ASR}	0	—	0	—	0	—	ns	
Row Address Hold Time	t _{RAH}	10	—	10	—	10	—	ns	
Column Address Set-up Time	t _{ASC}	0	—	0	—	0	—	ns	11
Column Address Hold Time	t _{CAH}	15	—	15	—	15	—	ns	11
Column Address Hold Time from RAS	t _{AR}	50	—	55	—	60	—	ns	
Column Address to RAS Lead Time	t _{RAL}	30	—	35	—	40	—	ns	
Read Command Set-up Time	t _{RCS}	0	—	0	—	0	—	ns	11
Read Command Hold Time	t _{RCH}	0	—	0	—	0	—	ns	8, 11
Read Command Hold Time referenced to RAS	t _{RRH}	0	—	0	—	0	—	ns	8

AC Characteristics (2/2)

(V_{CC} = 0.3 V ± 3.3 V, T_a = 0°C to 70°C) Note 1, 2, 3

Parameter	Symbol	MSM51V18160 A -60		MSM51V18160 A -70		MSM51V18160 A -80		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.		
Write Command Set-up Time	t _{WCS}	0	—	0	—	0	—	ns	9, 11
Write Command Hold Time	t _{WCH}	10	—	15	—	15	—	ns	11
Write Command Hold Time from RAS	t _{WCR}	45	—	55	—	60	—	ns	
Write Command Pulse Width	t _{WP}	10	—	15	—	15	—	ns	
OE Command Hold Time	t _{OEH}	15	—	20	—	20	—	ns	
Write Command to $\overline{\text{RAS}}$ Lead Time	t _{RWL}	15	—	20	—	20	—	ns	
Write Command to $\overline{\text{CAS}}$ Lead Time	t _{CWL}	15	—	20	—	20	—	ns	13
Data-in Set-up Time	t _{DS}	0	—	0	—	0	—	ns	10, 11
Data-in Hold Time	t _{DH}	15	—	15	—	15	—	ns	10, 11
Data-in Hold Time from RAS	t _{DHR}	50	—	55	—	60	—	ns	
OE to Data-in Delay Time	t _{OED}	15	—	15	—	15	—	ns	
$\overline{\text{CAS}}$ to $\overline{\text{WE}}$ Delay Time	t _{CWD}	35	—	45	—	45	—	ns	9
Column Address to $\overline{\text{WE}}$ Delay Time	t _{AWD}	50	—	60	—	65	—	ns	9
RAS to $\overline{\text{WE}}$ Delay Time	t _{RWD}	80	—	95	—	105	—	ns	9
CAS Precharge $\overline{\text{WE}}$ Delay Time	t _{CPWD}	55	—	65	—	70	—	ns	9
CAS Active Delay Time from RAS Precharge	t _{RPC}	5	—	5	—	5	—	ns	11
RAS to $\overline{\text{CAS}}$ Set-up Time ($\overline{\text{CAS}}$ before RAS)	t _{CSR}	5	—	5	—	5	—	ns	11
RAS to $\overline{\text{CAS}}$ Hold Time ($\overline{\text{CAS}}$ before RAS)	t _{CHR}	10	—	15	—	15	—	ns	12
CAS Precharge Time (Refresh Counter Test)	t _{CPT}	20	—	30	—	40	—	ns	14

- Notes:
1. A start-up delay of 200 μ s is required after power-up followed by a minimum of eight initialization cycles (RAS-only refresh or CAS before RAS refresh) before proper device operation is achieved.
 2. The AC characteristics assume $t_T = 5$ ns.
 3. V_{IH} (Min.) and V_{IL} (Max.) are reference levels for measuring input timing signals. Transition times (t_T) are measured between V_{IH} and V_{IL} .
 4. Measured with a load circuit equivalent to 1 TTL loads and 100 pF. Output timing reference levels are $V_{OH} = 2.0$ V and $V_{OL} = 0.8$ V.
 5. Operation within the t_{RCD} (Max.) limit ensures that t_{RAC} (Max.) can be met. t_{RCD} (Max.) is specified as a reference point only. If t_{RCD} is greater than the specified t_{RCD} (Max.) limit, access time is controlled by t_{CAC} .
 6. Operation within the t_{RAD} (Max.) limit ensures that t_{RAC} (Max.) can be met. t_{RAD} (Max.) is specified as a reference point only. If t_{RAD} is greater than the specified t_{RAD} (Max.) limit, access time is controlled by t_{AA} .
 7. t_{OFF} (Max.) and t_{OEZ} (Max.) define the time at which the output achieves the open circuit condition and are not referenced to output voltage levels.
 8. t_{RCH} or t_{RRH} must be satisfied for a read cycle.
 9. t_{WCS} , t_{CWD} , t_{RWD} , t_{AWD} and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} \geq t_{WCS}$ (Min.) the cycle is an early write cycle and the data out will remain open circuit (high impedance) throughout the entire cycle. If $t_{CWD} \geq t_{CWD}$ (Min.), $t_{RWD} \geq t_{RWD}$ (Min.), $t_{AWD} \geq t_{AWD}$ (Min.) and $t_{CPWD} \geq t_{CPWD}$ (Min.) the cycle is read modify write cycle and data out will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
 10. These parameters are referenced to \overline{UCAS} , \overline{LCAS} leading edge in an early write cycle and to \overline{WE} leading edge in a \overline{OE} control write cycle or a read modify write cycle.
 11. These parameters are determined by the earlier falling edge of \overline{UCAS} or \overline{LCAS} .
 12. These parameters are determined by the later rising edge of \overline{UCAS} or \overline{LCAS} .
 13. t_{CWL} should be satisfied by both \overline{UCAS} or \overline{LCAS} .
 14. t_{CP} and t_{CPT} are determined by the time that both \overline{UCAS} or \overline{LCAS} are high.

See ADDENDUM A for AC Timing Waveforms

TIMING WAVEFORM A

for MSM5116160A

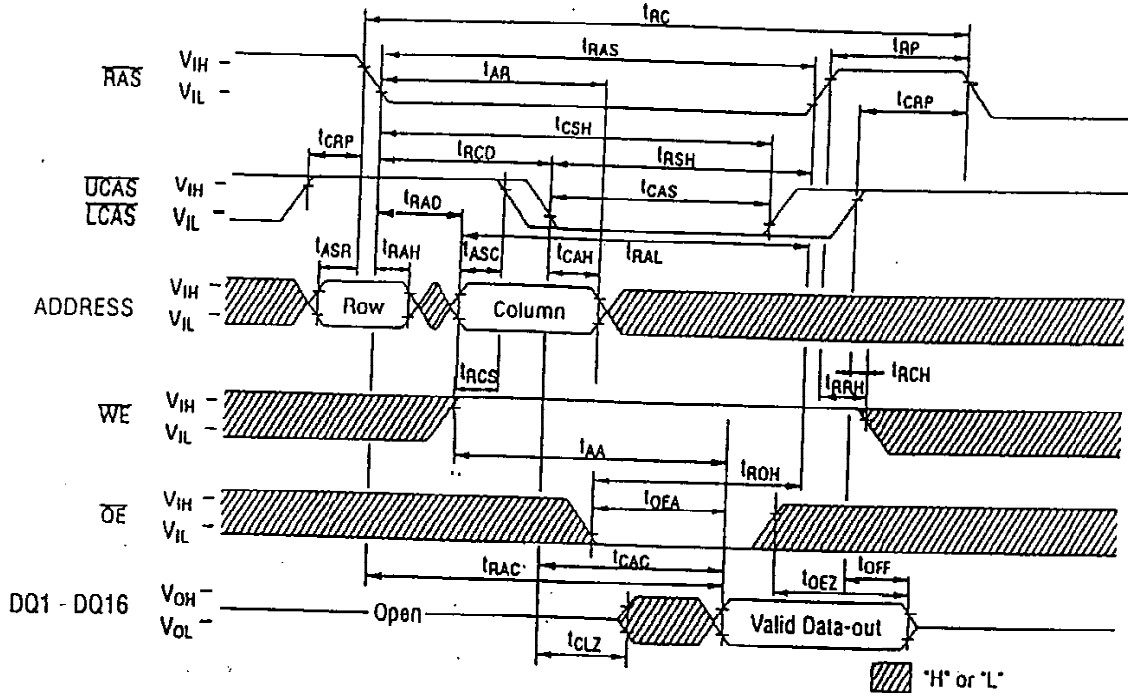
MSM5118160A

MSM51V16160A

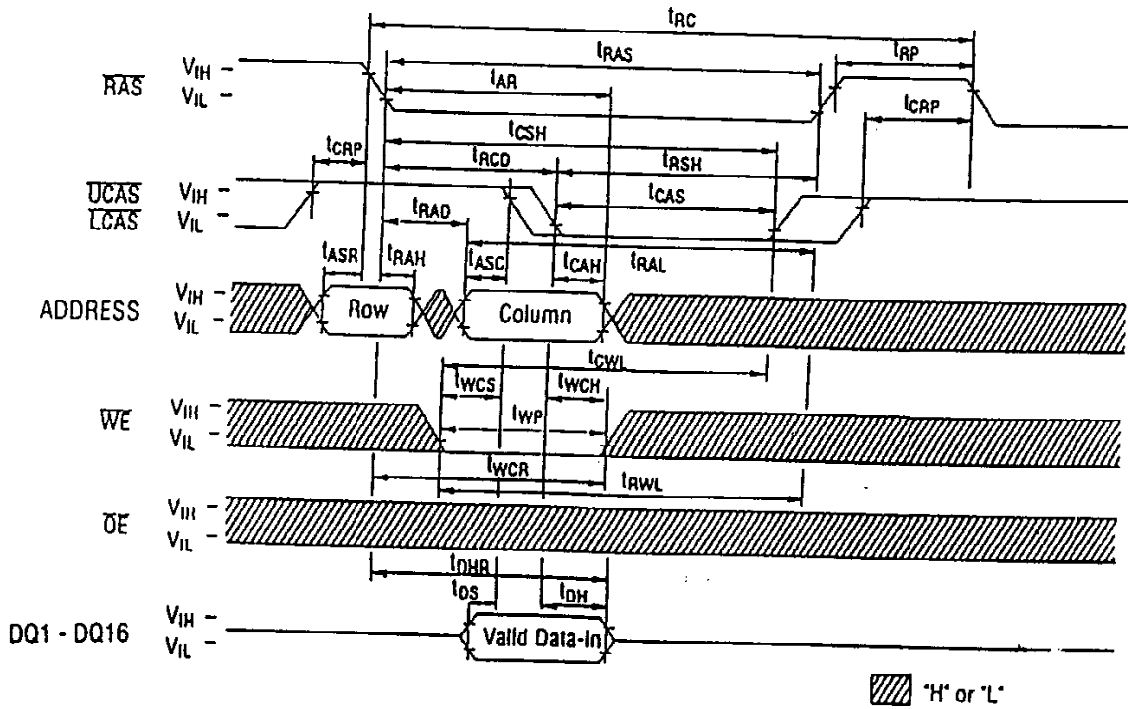
MSM51V18160A

TIMING WAVEFORM

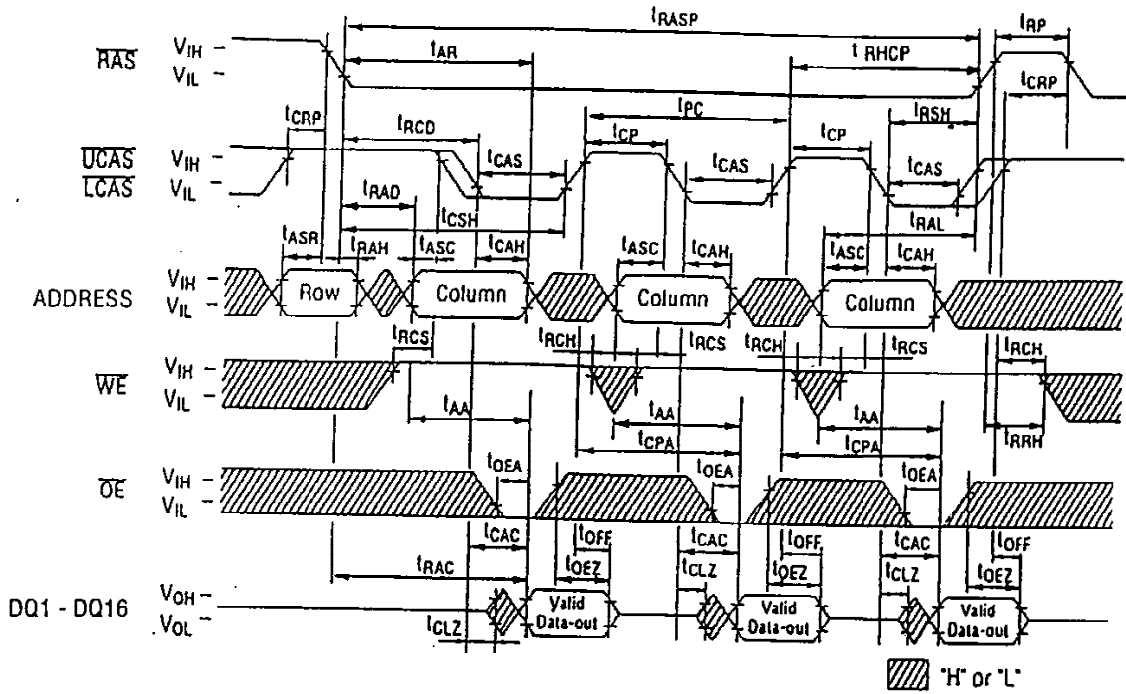
Read Cycle



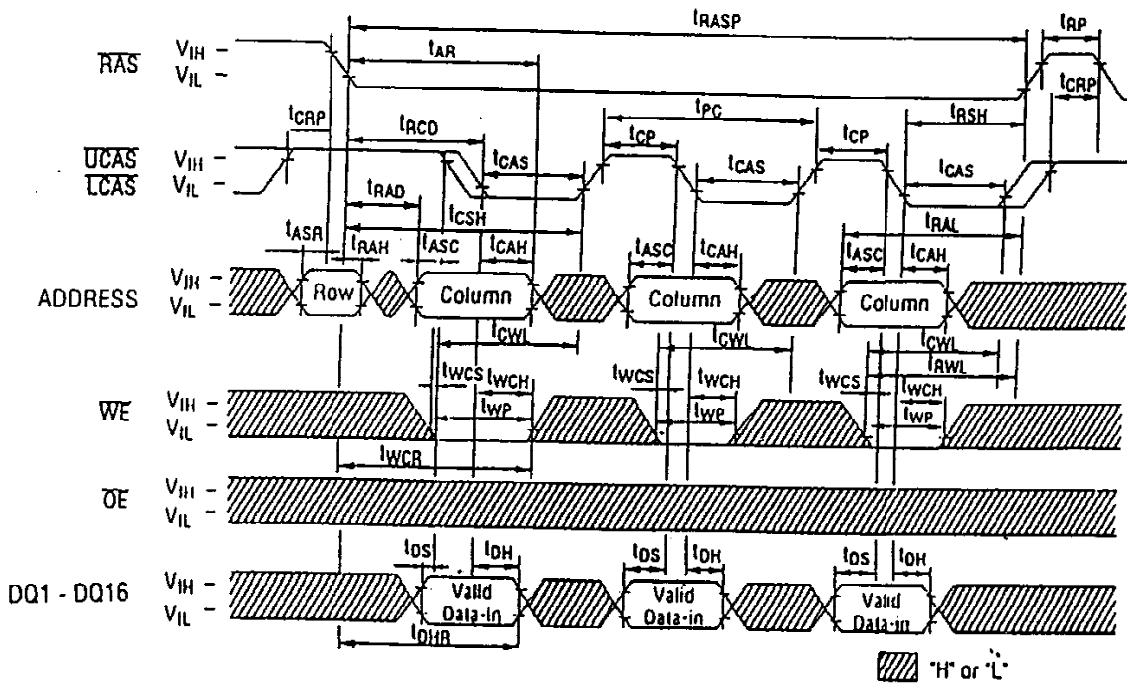
Write Cycle (Early Write)



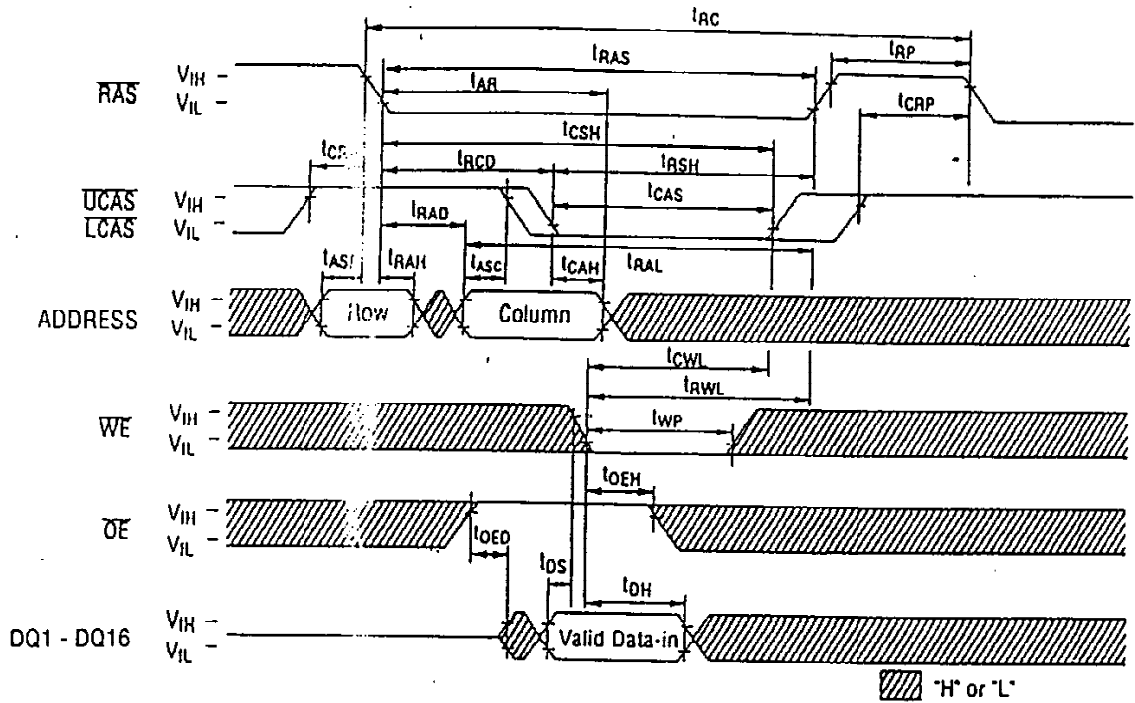
Fast Page Mode Read Cycle



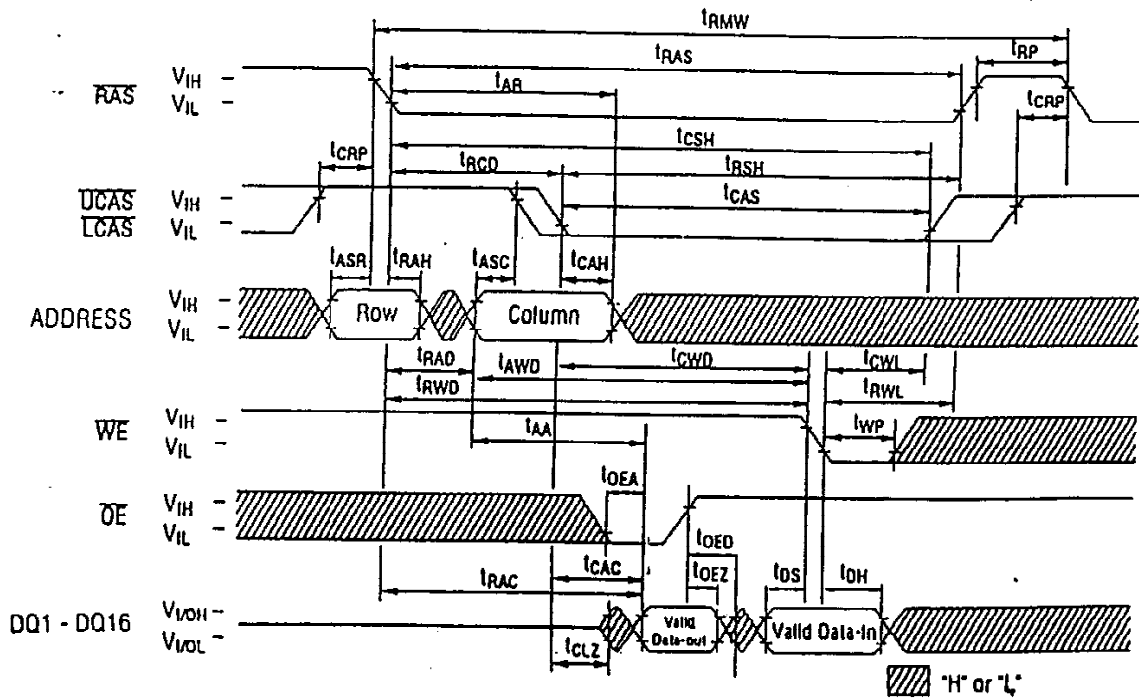
Fast Page Mode Write Cycle (Early Write)



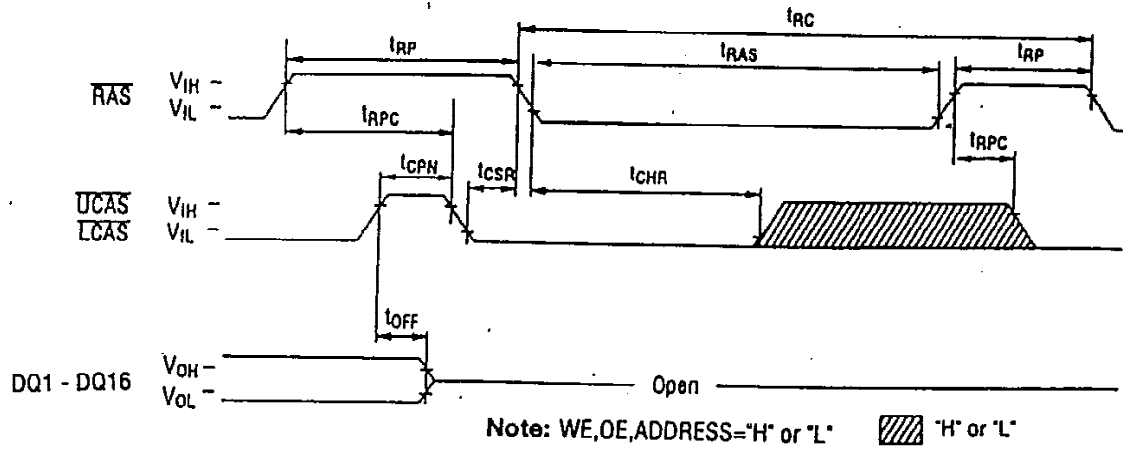
Write Cycle (\overline{OE} Control Write)



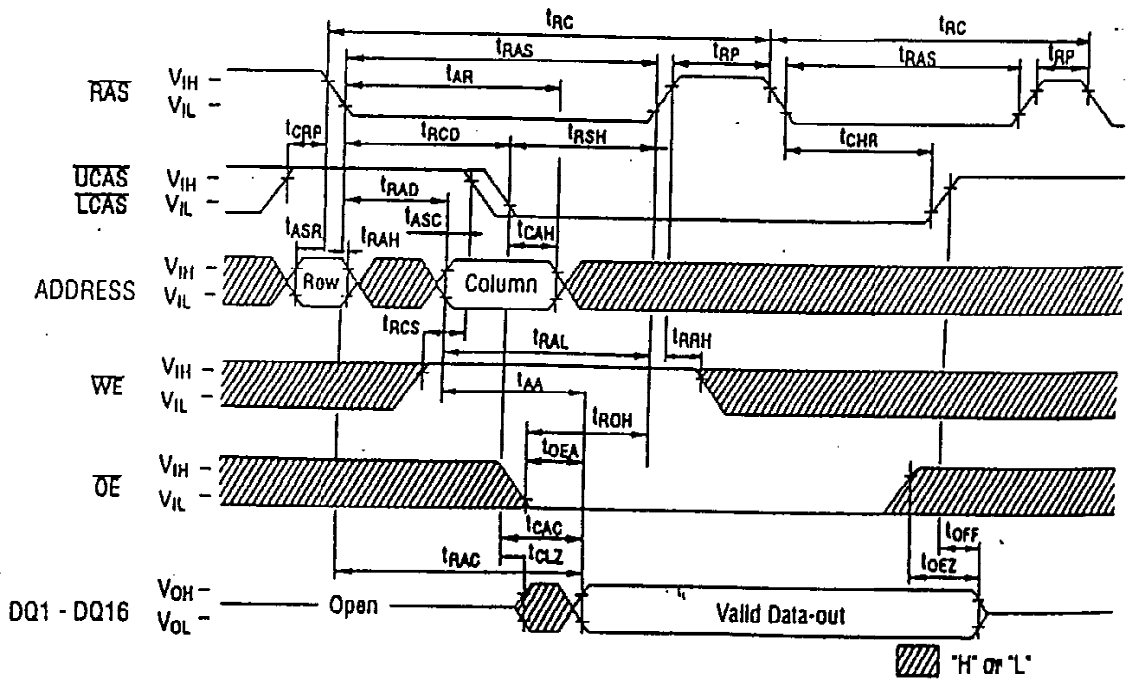
Read Modify Write Cycle



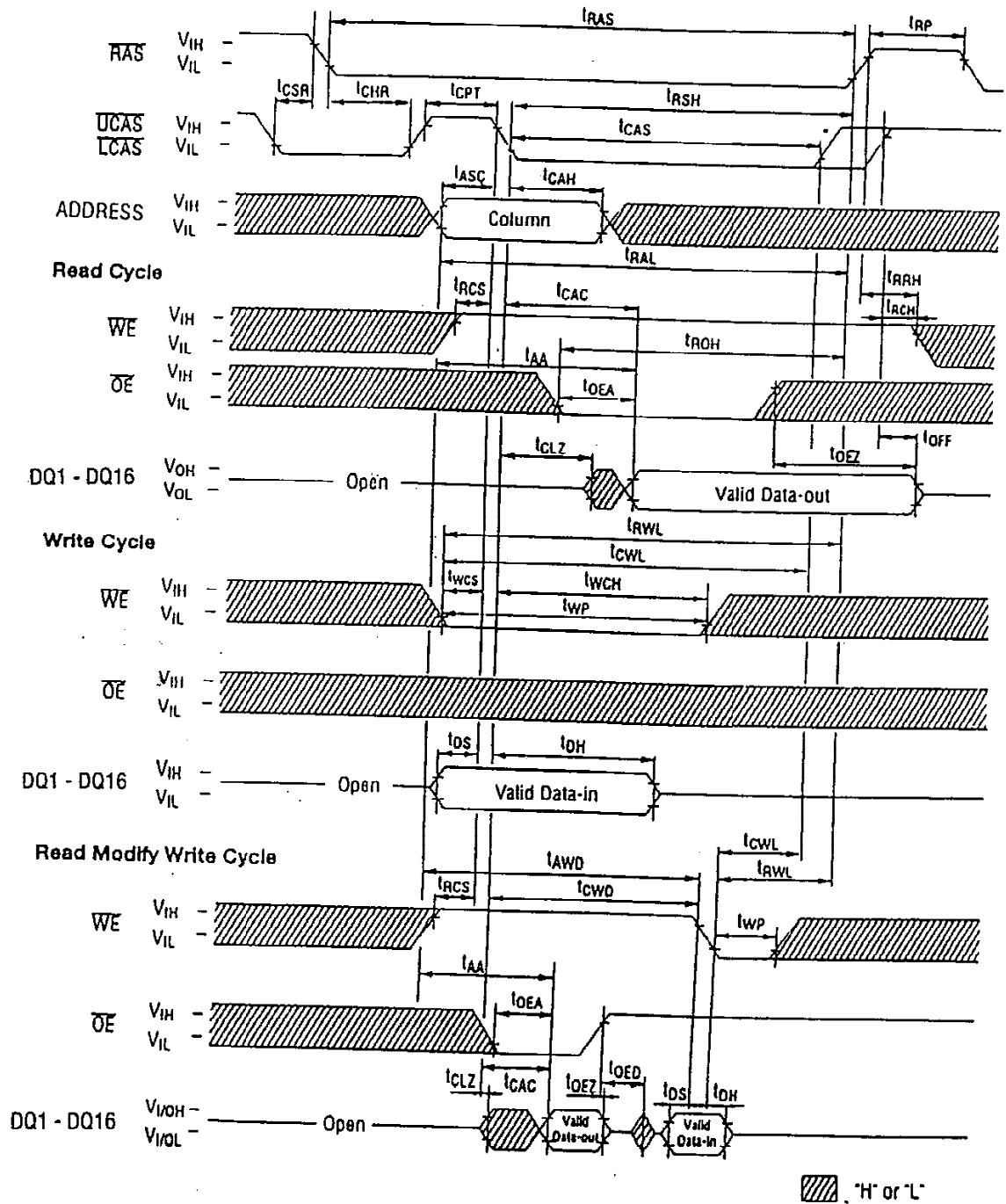
CAS Before RAS Auto Refresh Cycle



Hidden Refresh Read Cycle



CAS Before RAS Refresh Counter Test Cycle



Hidden Refresh Write Cycle

